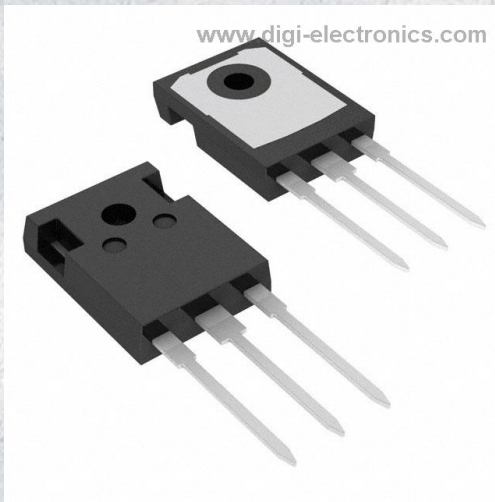


FCH25N60N Datasheet



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	FCH25N60N-DG
Manufacturer	onsemi
Manufacturer Product Number	FCH25N60N
Description	MOSFET N-CH 600V 25A TO247-3
Detailed Description	N-Channel 600 V 25A (Tc) 216W (Tc) Through Hole TO-247-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

FCH25N60N

Series:

SupreMOS™

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

600 V

Drive Voltage (Max Rds On, Min Rds On):

10V

Vgs(th) (Max) @ Id:

4V @ 250µA

Vgs (Max):

±30V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

TO-247-3

Base Product Number:

FCH25N60

Manufacturer:

onsemi

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

25A (Tc)

Rds On (Max) @ Id, Vgs:

126mOhm @ 12.5A, 10V

Gate Charge (Qg) (Max) @ Vgs:

74 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

3352 pF @ 100 V

Power Dissipation (Max):

216W (Tc)

Mounting Type:

Through Hole

Package / Case:

TO-247-3

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

Not Applicable

ECCN:

EAR99

MOSFET – N-Channel, SUPREMOS

600 V, 25 A, 126 mΩ

FCH25N60N

Description

The SUPREMOS[®] MOSFET is ON Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest R_{sp} on-resistance, superior switching performance and ruggedness. SUPREMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.

Features

- R_{DS(on)} = 108 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 12.5 A
- Ultra Low Gate Charge (Typ. Q_g = 57 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 262 pF)
- 100% Avalanche Tested
- This Device is Pb-Free and is RoHS Compliant

Applications

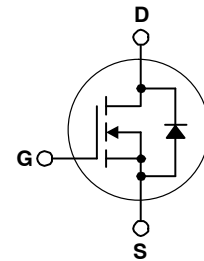
- Solar Inverter
- AC-DC Power Supply



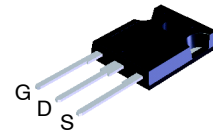
ON Semiconductor[®]

www.onsemi.com

V _{DS}	R _{DS(ON)} MAX	I _D MAX
600 V	126 mΩ @ 10 V	25 A

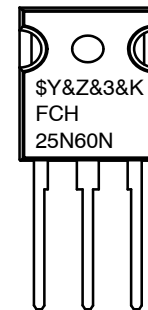


N-CHANNEL MOSFET



TO-247-3LD
CASE 340CK

MARKING DIAGRAM



\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FCH25N60N	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FCH25N60N**ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		600	V
V_{GSS}	Gate to Source Voltage		± 30	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	25	A
		- Continuous ($T_C = 100^\circ\text{C}$)	16	
I_{DM}	Drain Current	- Pulsed (Note 1)	75	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		861	mJ
I_{AR}	Avalanche Current (Note 1)		8.3	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		2.2	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		20	
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	216	W
		- Derate above 25°C	1.72	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to + 150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Second		300	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. $I_{AS} = 8.3\text{ A}$, $R_G = 25\ \Omega$, starting $T_J = 25\ ^\circ\text{C}$
3. $I_{SD} \leq 25\text{ A}$, $di/dt \leq 200\text{ A/s}$, $V_{DD} \leq 380\text{ V}$, starting $T_J = 25\ ^\circ\text{C}$

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Package Method	Reel Size	Tape Width	Quantity
FCH25N60N	FCH25N60N	TO-247-3LD	Tube	N/A	N/A	30 Units

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.58	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

FCH25N60N**ELECTRICAL CHARACTERISTICS** ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
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OFF CHARACTERISTICS

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 1\text{ mA}, V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$	600	–	–	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 1\text{ mA}$, Referenced to 25°C	–	0.74	–	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}$	–	–	10	μA
		$V_{DS} = 480\text{ V}, T_J = 125^\circ\text{C}$	–	–	100	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	–	–	± 100	nA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	2.0	–	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 12.5\text{ A}$	–	0.108	0.126	Ω

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	–	2520	3352	pF
C_{oss}	Output Capacitance		–	103	137	pF
C_{rss}	Reverse Transfer Capacitance		–	3.2	5	pF
C_{oss}	Output Capacitance	$V_{DS} = 380\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	–	55	–	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$	–	262	–	pF
$Q_{g(tot)}$	Total Gate Charge at 10 V	$V_{DS} = 380\text{ V}, I_D = 12.5\text{ A}, V_{GS} = 10\text{ V}$ (Note 4)	–	57	74	nC
Q_{gs}	Gate to Source Gate Charge		–	10	–	nC
Q_{gd}	Gate to Drain "Miller" Charge		–	18	–	nC
ESR	Equivalent Series Resistance(G-S)	$f = 1\text{ MHz}$	–	1	–	Ω

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 380\text{ V}, I_D = 12.5\text{ A}, V_{GS} = 10\text{ V}, R_G = 4.7\text{ }\Omega$ (Note 4)	–	21	52	ns
t_r	Turn-On Rise Time		–	22	54	ns
$t_{d(off)}$	Turn-Off Delay Time		–	68	146	ns
t_f	Turn-Off Fall Time		–	5	20	ns

DRAIN-SOURCE DIODE CHARACTERISTICS

I_S	Maximum Continuous Drain to Source Diode Forward Current	–	–	25	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	–	–	75	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_{SD} = 12.5\text{ A}$	–	–	1.2	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_{SD} = 12.5\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}$	–	370	–	ns
Q_{rr}	Reverse Recovery Charge		–	7	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

FCH25N60N

TYPICAL CHARACTERISTICS

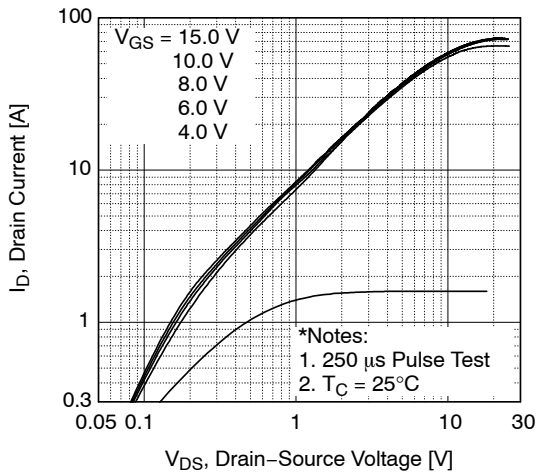


Figure 1. On-Region Characteristics

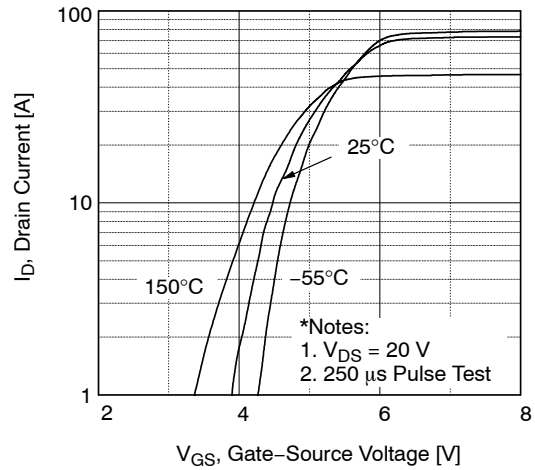


Figure 2. Transfer Characteristics

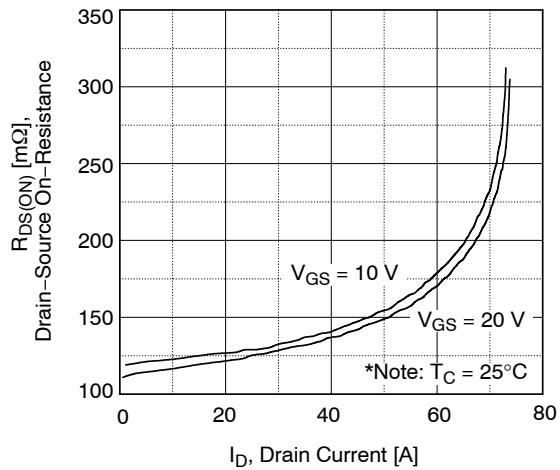


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

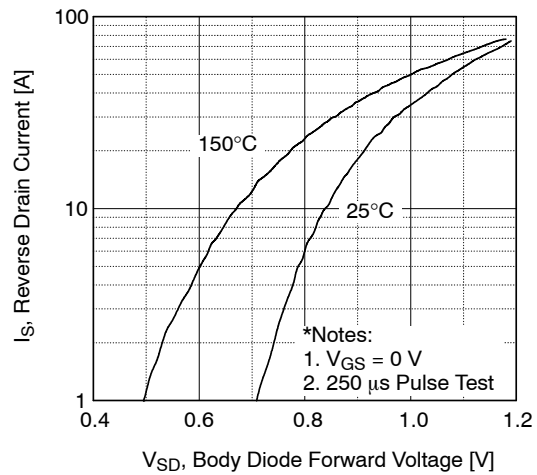


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

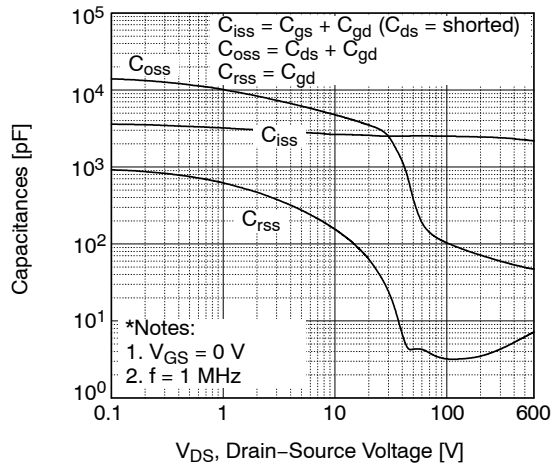


Figure 5. Capacitance Characteristics

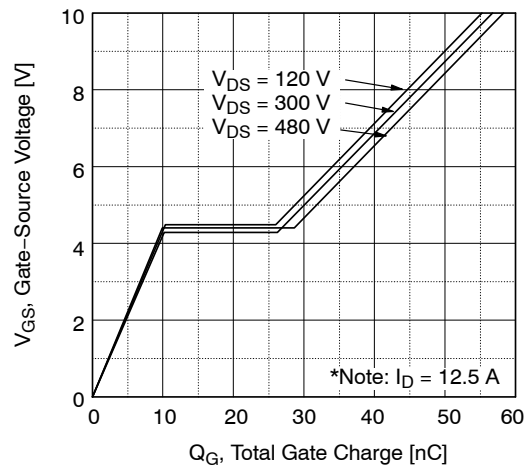


Figure 6. Gate Charge Characteristics

FCH25N60N

TYPICAL CHARACTERISTICS

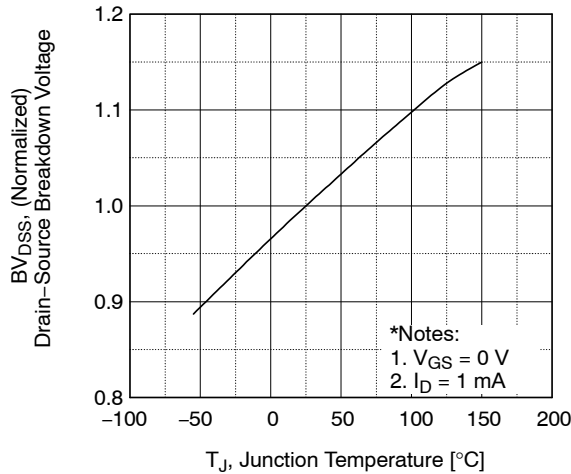


Figure 7. Breakdown Voltage Variation vs. Temperature

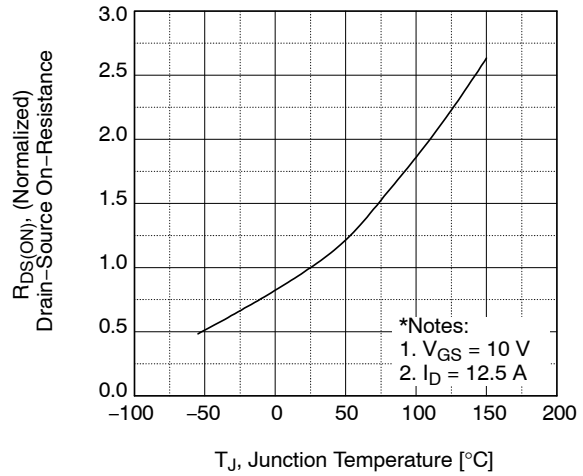


Figure 8. On-Resistance Variation vs. Temperature

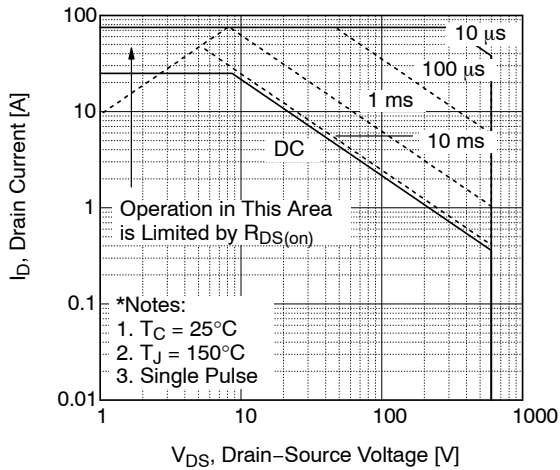


Figure 9. Maximum Safe Operating Area

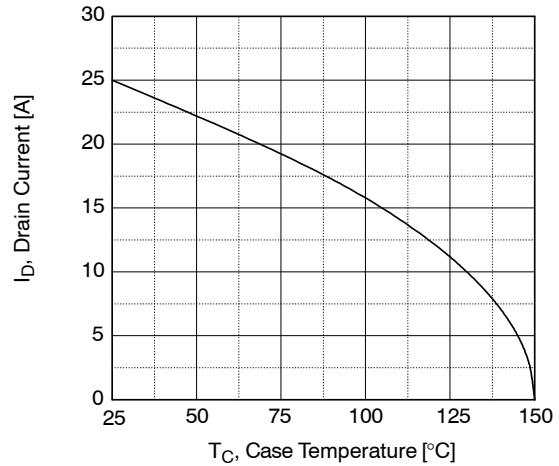


Figure 10. Maximum Drain Current vs. Case Temperature

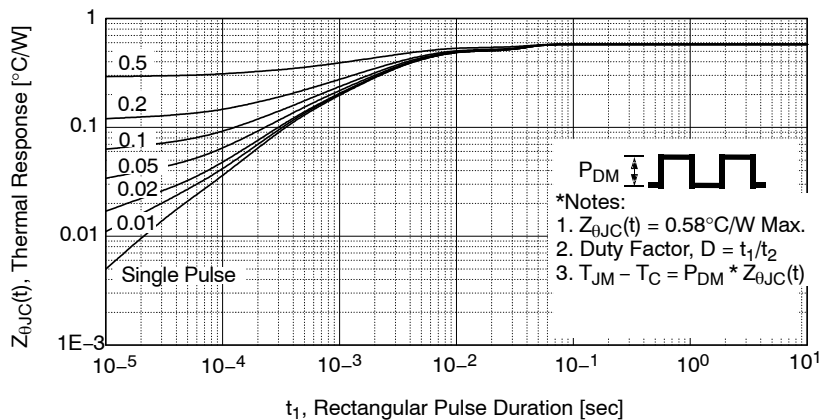


Figure 11. Transient Thermal Response Curve

FCH25N60N

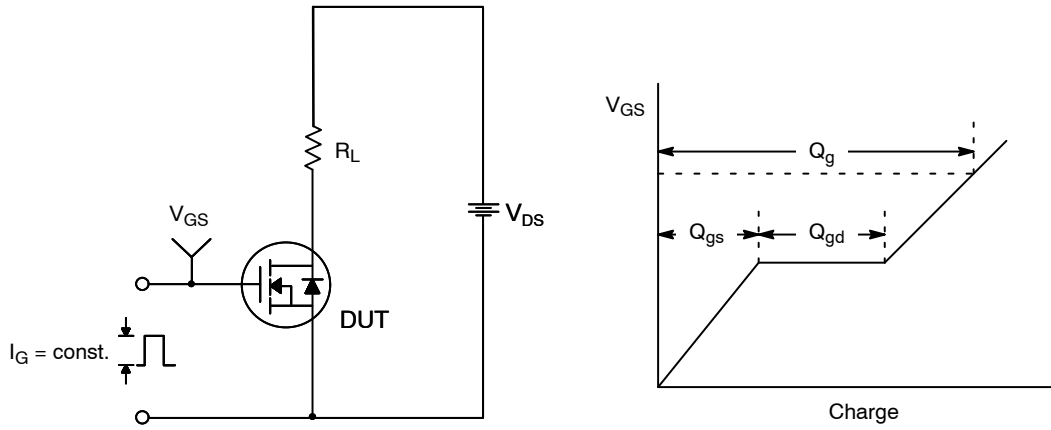


Figure 12. Gate Charge Test Circuit & Waveform

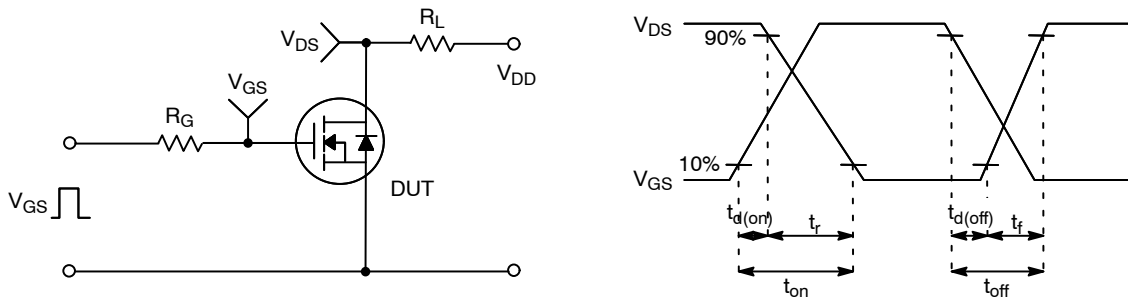


Figure 13. Resistive Switching Test Circuit & Waveforms

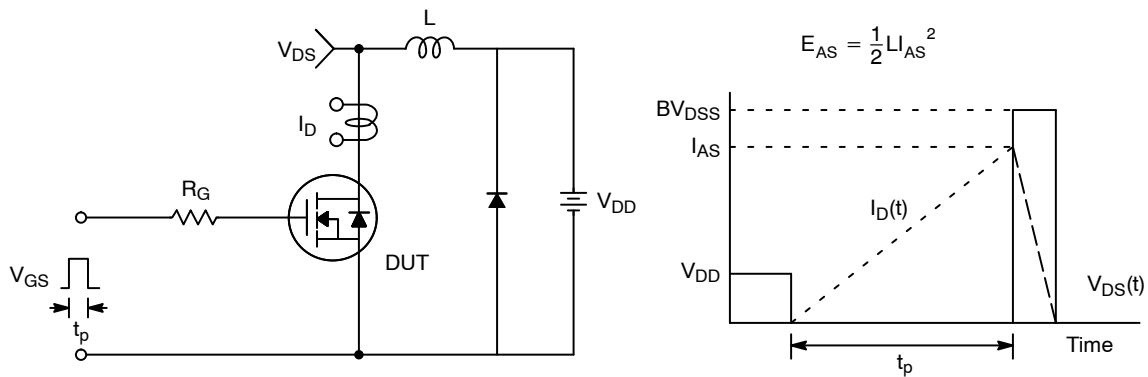


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

FCH25N60N

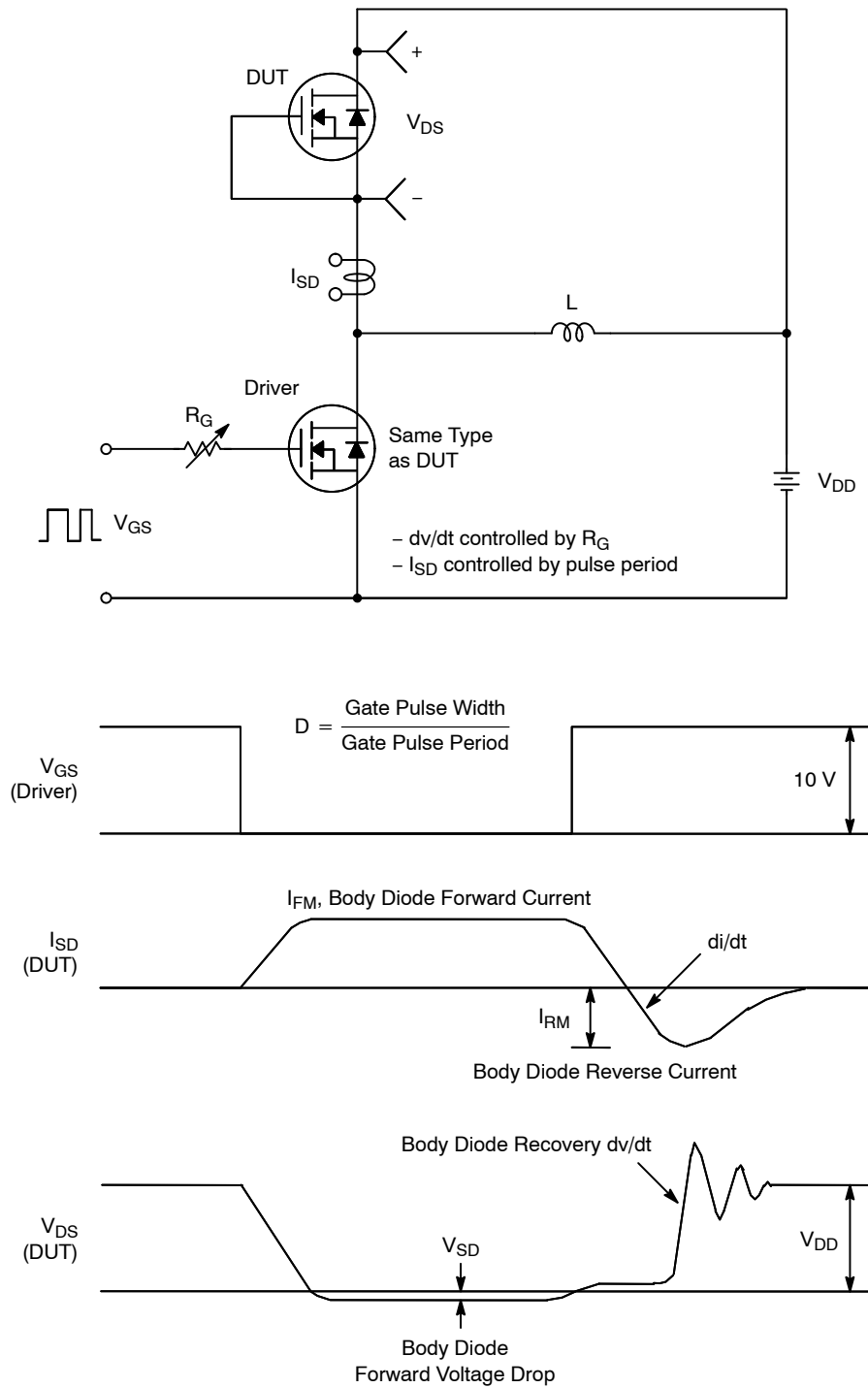
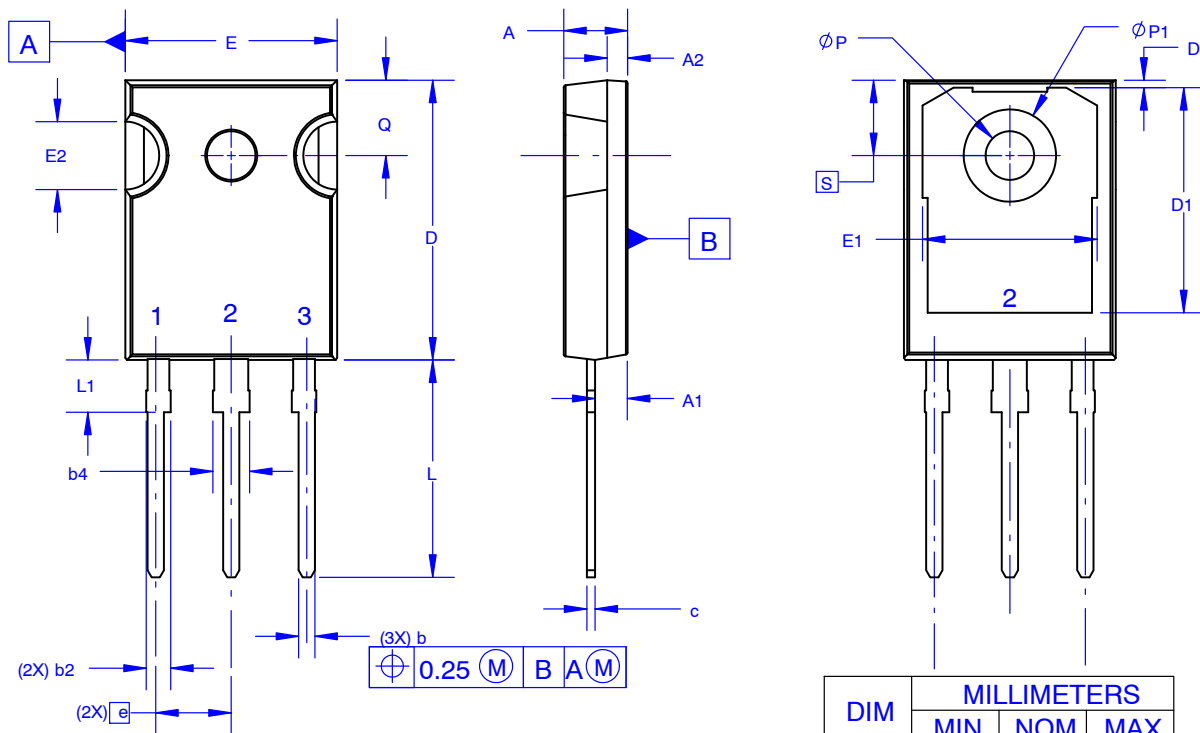


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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TO-247-3LD SHORT LEAD
CASE 340CK
ISSUE A

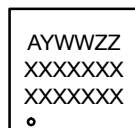
DATE 31 JAN 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	5.56	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
ØP1	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

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DESCRIPTION:	TO-247-3LD SHORT LEAD	PAGE 1 OF 1

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